

ERRATUM

**E. Kamińska, A. Piotrowska, J. Jasiński, J. Kozubowski, A. Barcz,
K. Gołaszewska, M.D. Bremser, R.F. Davis**
Interfacial Microstructure of Ni/Si-Based Ohmic Contacts to GaN
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Due to technical error some artefact lines occurred below the photograph in Figure 2 (a). The proper copy of Fig. 2 is as shown below. The Production Editor regrets the mistake.

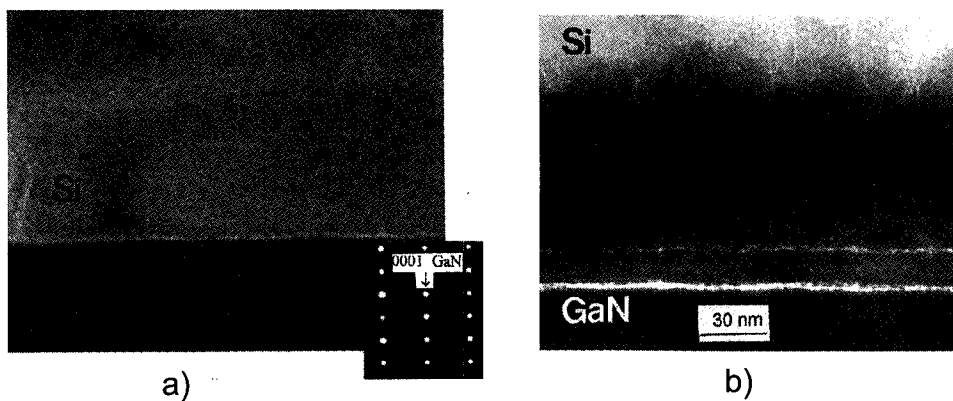


Fig. 2. (a) XTEM image of the GaN/Ni/Si contact annealed at 500°C, (b) HREM lattice image of the interface of the GaN/Ni/Si contact annealed at 500°C.